

# 1SS294

## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

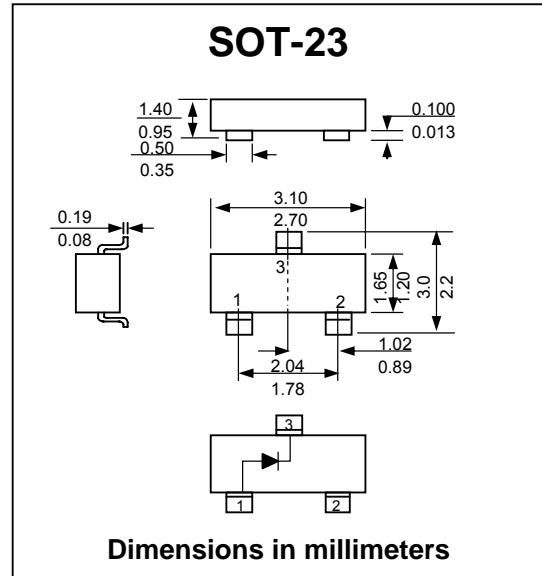
**PRV : 45 Volts**  
**I<sub>o</sub> : 100 mA**

**FEATURES :**

- \* Small surface mounting type
- \* Low forward voltage
- \* Low reverse current
- \* Pb / RoHS Free

**MECHANICAL DATA :**

- \* Case : SOT-23 plastic Case
- \* Marking Code : " XM "



**MAXIMUM RATINGS AND THERMAL CHARACTERISTICS** (Ta = 25 °C)

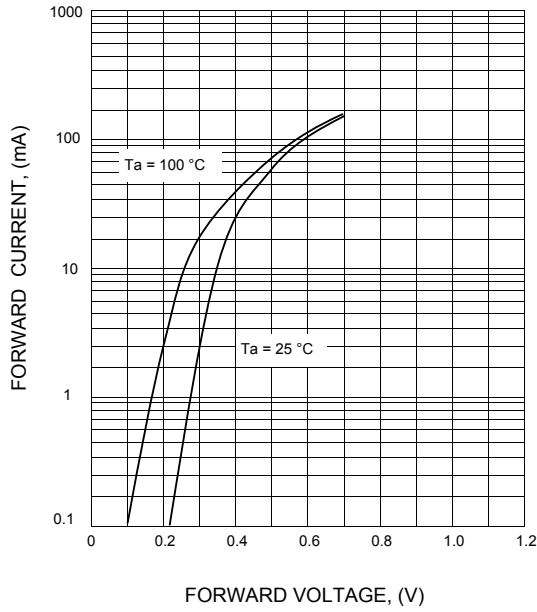
Parameter	Symbol	Value	Unit
Maximum Peak Reverse Voltage	V <sub>RM</sub>	45	V
Reverse Voltage	V <sub>R</sub>	40	V
Maximum Peak Forward Current	I <sub>FM</sub>	300	mA
Average Forward Current	I <sub>F(AV)</sub>	100	mA
Power Dissipation	P <sub>D</sub>	150	mW
Junction Temperature	T <sub>J</sub>	125	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +125	°C

**ELECTRICAL CHARACTERISTICS** (Ta = 25 °C)

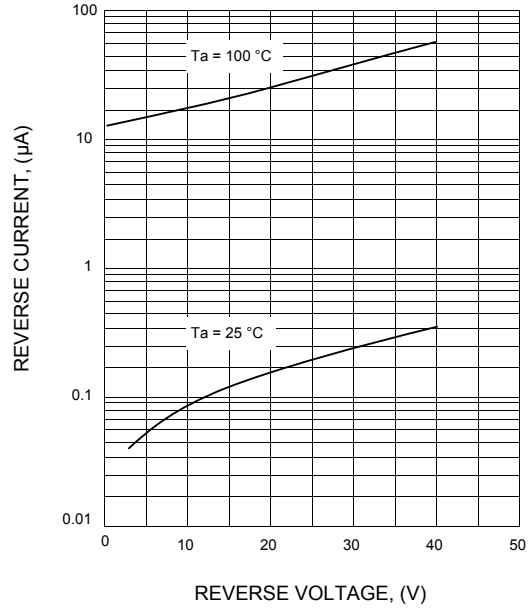
Parameter	Test Condition	Symbol	Min.	Max.	Unit
Forward Voltage	I <sub>F</sub> = 100 mA	V <sub>F</sub>	-	0.6	V
Reverse Current	V <sub>R</sub> = 40 V	I <sub>R</sub>	-	5	µA
Total Capacitance	V <sub>R</sub> = 0 V, f = 1 MHz	C <sub>T</sub>	-	25	pF

### RATINGS AND CHARACTERISTIC CURVES ( 1SS294 )

**FIG.1 - FORWARD CURRENT VS. FORWARD VOLTAGE**



**FIG.2 - REVERSE CURRENT VS. REVERSE VOLTAGE**



**FIG.3 - TOTAL CAPACITANCE VS. REVERSE VOLTAGE**

